

☐ Search Results

BROWSE

SEARCH

IEEE XPLORE GUIDE

SUPPORT

Results for "((diffusion <near/3> size) <and> simulat??? <and> isolation) <in> pdfdata"

Your search matched 9 of 1436708 documents.

A maximum of 100 results are displayed, 25 to a page, sorted by Relevance in Descending order.


 e-mail
  printer friendly

» Search Options

[View Session History](#)[New Search](#)

Modify Search

((diffusion <near/3> size) <and> simulat??? <and> isolation) <in> pdfdata

Search ☐ Check to search only within this results setDisplay Format: ☒ Citation ☐ Citation & Abstract
☐ view selected items
 [Select All](#)
[Deselect All](#)

IEEE JNL IEEE Journal or Magazine

IEE JNL IEE Journal or Magazine

IEEE CNF IEEE Conference Proceeding

IEE CNF IEE Conference Proceeding

IEEE STD IEEE Standard

- ☐ 1. 1982 IEEE Ultrasonics Symposium Abstracts
Sonics and Ultrasonics, IEEE Transactions on
 Volume 30, Issue 3, May 1983 Page(s):184 - 227
AbstractPlus | Full Text: [PDF\(5672 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 2. A Multiplexing/Demultiplexing Transceiver for 565-Mbit/s Fiber-Optic Links
 Mudd, M.S.J.; Taylor, D.G.; Wood, I.C.; Childs, J.C.; Saul, P.H.;
Solid-State Circuits, IEEE Journal of
 Volume 20, Issue 3, Jun 1985 Page(s):708 - 714
AbstractPlus | Full Text: [PDF\(1136 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 3. Experimental results and modeling techniques for substrate noise in mixed-signal integrated circuits
 Su, D.K.; Loinaz, M.J.; Masui, S.; Wooley, B.A.;
Solid-State Circuits, IEEE Journal of
 Volume 28, Issue 4, April 1993 Page(s):420 - 430
 Digital Object Identifier 10.1109/4.210024
AbstractPlus | Full Text: [PDF\(1048 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 4. A 200 MHz CMOS Q-enhanced LC bandpass filter
 Kuhn, W.B.; Stephenson, F.W.; Elshabini-Riad, A.;
Solid-State Circuits, IEEE Journal of
 Volume 31, Issue 8, Aug. 1996 Page(s):1112 - 1122
 Digital Object Identifier 10.1109/4.508258
AbstractPlus | [References](#) | Full Text: [PDF\(1120 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 5. Single event effects in static and dynamic registers in a 0.25 μ m CMOS technology
 Faccio, F.; Kloukinas, K.; Marchioro, A.; Calin, T.; Cosculluela, J.; Nicolaidis, M.; Velazco, R.;
Nuclear Science, IEEE Transactions on
 Volume 46, Issue 6, Dec. 1999 Page(s):1434 - 1439
 Digital Object Identifier 10.1109/23.819104
AbstractPlus | Full Text: [PDF\(404 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 6. Considerations in engineering parallel multiobjective evolutionary algorithms
 Van Veldhuizen, D.A.; Zydallis, J.B.; Lamont, G.B.;
Evolutionary Computation, IEEE Transactions on

Volume 7, Issue 2, April 2003 Page(s):144 - 173
Digital Object Identifier 10.1109/TEVC.2003.810751

[AbstractPlus](#) | [References](#) | [Full Text: PDF\(998 KB\)](#) IEEE JNL
[Rights and Permissions](#)

- ☐ 7. **Highly effective junction isolation structures for PICs based on standard CMOS Process**
Starke, T.K.H.; Holland, P.M.; Hussain, S.; Jamal, W.M.; Mawby, P.A.; Igic, P.M.;
[Electron Devices, IEEE Transactions on](#)

Volume 51, Issue 7, July 2004 Page(s):1178 - 1184
Digital Object Identifier 10.1109/TED.2004.829895

[AbstractPlus](#) | [References](#) | [Full Text: PDF\(552 KB\)](#) IEEE JNL
[Rights and Permissions](#)

- ☐ 8. **High-density static bipolar memory**
Wiedmann, S.;
[Solid-State Circuits Conference, Digest of Technical Papers, 1973 IEEE International](#)
Volume XVI, Feb 1973 Page(s):56 - 57

[AbstractPlus](#) | [Full Text: PDF\(368 KB\)](#) IEEE CNF
[Rights and Permissions](#)

- ☐ 9. **Advanced junction isolation structures for Power Integrated Circuit technology**
Mawby, P.A.; Starke, T.K.H.; Holland, P.M.; Hussain, S.; Jamal, W.M.; Igic, P.M.;
[Microelectronics, 2004. 24th International Conference on](#)
Volume 1, 16-19 May 2004 Page(s):17 - 22 vol.1

[AbstractPlus](#) | [Full Text: PDF\(463 KB\)](#) IEEE CNF
[Rights and Permissions](#)

[Help](#) [Contact Us](#) [Privacy & Security](#) [IEEE.org](#)

© Copyright 2006 IEEE – All Rights Reserved

Indexed by
 Inspec®



Welcome United States Patent and Trademark Office

☐ Search Results

[BROWSE](#)

[SEARCH](#)

[IEEE XPLORE GUIDE](#)

[SUPPORT](#)

Results for "((diffusion <near/3> length) <and> simulat??? <and> isolation <and> correct?..."
Your search matched 47 of 1436708 documents.
A maximum of 100 results are displayed, 25 to a page, sorted by Relevance in Descending order.

[e-mail](#) [printer friendly](#)

» Search Options

[View Session History](#)

[New Search](#)

Modify Search

☐ Check to search only within this results set

Display Format: ☒ Citation ☐ Citation & Abstract

» Key

- IEEE JNL IEEE Journal or Magazine
- IEE JNL IEE Journal or Magazine
- IEEE CNF IEEE Conference Proceeding
- IEE CNF IEE Conference Proceeding
- IEEE STD IEEE Standard

[Select All](#) [Deselect All](#)

1-25 | [26-47](#)

- ☐ 1. Design of wide-emitter single-mode laser diodes
Jun Jun Lim; Benson, T.M.; Larkins, E.C.;
[Quantum Electronics, IEEE Journal of](#)
Volume 41, Issue 4, April 2005 Page(s):506 - 516
Digital Object Identifier 10.1109/JQE.2005.843924
[AbstractPlus](#) | [References](#) | Full Text: [PDF](#)(968 KB) IEEE JNL
[Rights and Permissions](#)
- ☐ 2. Static and dynamic properties of InGaAsP-InP distributed feedback lasers-a detailed comparison between experiment and theory
Hansmann, S.; Walter, H.; Hillmer, H.; Burkhard, H.;
[Quantum Electronics, IEEE Journal of](#)
Volume 30, Issue 11, Nov. 1994 Page(s):2477 - 2484
Digital Object Identifier 10.1109/3.333698
[AbstractPlus](#) | Full Text: [PDF](#)(668 KB) IEEE JNL
[Rights and Permissions](#)
- ☐ 3. Marvelous MEMS
Bryzek, J.; Roundy, S.; Bircumshaw, B.; Chung, C.; Castellino, K.; Stetter, J.R.; Vestel, M.;
[Circuits and Devices Magazine, IEEE](#)
Volume 22, Issue 2, March-April 2006 Page(s):8 - 28
Digital Object Identifier 10.1109/MCD.2006.1615241
[AbstractPlus](#) | Full Text: [PDF](#)(6020 KB) IEEE JNL
[Rights and Permissions](#)
- ☐ 4. 1977 IEEE Ultrasonics Symposium Abstracts
[Sonics and Ultrasonics, IEEE Transactions on](#)
Volume 25, Issue 4, Jul 1978 Page(s):230 - 267
[AbstractPlus](#) | Full Text: [PDF](#)(4960 KB) IEEE JNL
[Rights and Permissions](#)
- ☐ 5. Optical and interferometric lithography - nanotechnology enablers
Brueck, S.R.J.;
[Proceedings of the IEEE](#)
Volume 93, Issue 10, Oct. 2005 Page(s):1704 - 1721
Digital Object Identifier 10.1109/JPROC.2005.853538
[AbstractPlus](#) | Full Text: [PDF](#)(3768 KB) IEEE JNL
[Rights and Permissions](#)
- ☐ 6. Back cover
[Electron Device Letters, IEEE](#)

Volume 7, Issue 12, Dec 1986 Page(s):c4 - c4

Full Text: [PDF\(3008 KB\)](#) IEEE JNL

[Rights and Permissions](#)

- ☐ 7. **Back cover**
[Electron Devices, IEEE Transactions on](#)
Volume 15, Issue 9, Sep 1968 Page(s):c4 - c4
Full Text: [PDF\(2072 KB\)](#) IEEE JNL
[Rights and Permissions](#)

- ☐ 8. **Back cover**
[Electron Devices, IEEE Transactions on](#)
Volume 25, Issue 12, Dec 1978 Page(s):c4 - c4
Full Text: [PDF\(3560 KB\)](#) IEEE JNL
[Rights and Permissions](#)

- ☐ 9. **Back cover**
[Electron Devices, IEEE Transactions on](#)
Volume 26, Issue 12, Dec 1979 Page(s):c4 - c4
Full Text: [PDF\(6512 KB\)](#) IEEE JNL
[Rights and Permissions](#)

- ☐ 10. **Back cover**
[Electron Devices, IEEE Transactions on](#)
Volume 27, Issue 12, Dec 1980 Page(s):c4 - c4
Full Text: [PDF\(6480 KB\)](#) IEEE JNL
[Rights and Permissions](#)

- ☐ 11. **Back cover**
[Electron Devices, IEEE Transactions on](#)
Volume 29, Issue 12, Dec 1982 Page(s):c4 - c4
Full Text: [PDF\(5112 KB\)](#) IEEE JNL
[Rights and Permissions](#)

- ☐ 12. **An investigation of the intrinsic delay (speed limit) in MTL/I²L**
Berger, H.H.; Helwig, K.;
[Electron Devices, IEEE Transactions on](#)
Volume 26, Issue 4, Apr 1979 Page(s):405 - 415
[AbstractPlus](#) | Full Text: [PDF\(1336 KB\)](#) IEEE JNL
[Rights and Permissions](#)

- ☐ 13. **Variation of diffusion length with processing in dielectrically isolated π -silicon tubs**
Burk, D.E.; Flower, G.M.; Sang-Sun Lee;
[Electron Devices, IEEE Transactions on](#)
Volume 33, Issue 11, Nov 1986 Page(s):1678 - 1682
[AbstractPlus](#) | Full Text: [PDF\(464 KB\)](#) IEEE JNL
[Rights and Permissions](#)

- ☐ 14. **Back cover**
[Electron Devices, IEEE Transactions on](#)
Volume 34, Issue 12, Dec 1987 Page(s):c4 - c4
Full Text: [PDF\(7168 KB\)](#) IEEE JNL
[Rights and Permissions](#)

- ☐ 15. **Back cover**
[Electron Devices, IEEE Transactions on](#)
Volume 30, Issue 12, Dec 1983 Page(s):c4 - c4
Full Text: [PDF\(5392 KB\)](#) IEEE JNL
[Rights and Permissions](#)

- ☐ 16. A fully scaled submicrometer NMOS technology using direct-write E-beam lithography
Wordeman, M.R.; Schweighart, A.M.; Dennard, R.H.; Sai-Halasz, G.; Molzen, W.W.;
[Electron Devices, IEEE Transactions on](#)
Volume 32, Issue 11, Nov 1985 Page(s):2214 - 2223
[AbstractPlus](#) | Full Text: [PDF\(1544 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 17. Back cover
[Electron Devices, IEEE Transactions on](#)
Volume 33, Issue 12, Dec 1986 Page(s):c4 - c4
Full Text: [PDF\(5304 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 18. Measurement of steady-state minority-carrier transport parameters in heavily doped n-type silicon
del Alamo, J.A.; Swanson, R.M.;
[Electron Devices, IEEE Transactions on](#)
Volume 34, Issue 7, Jul 1987 Page(s):1580 - 1589
[AbstractPlus](#) | Full Text: [PDF\(1144 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 19. VLSI Process modeling—SUPREM III
Ho, C.P.; Plummer, J.D.; Hansen, S.E.; Dutton, R.W.;
[Electron Devices, IEEE Transactions on](#)
Volume 30, Issue 11, Nov 1983 Page(s):1438 - 1453
[AbstractPlus](#) | Full Text: [PDF\(1960 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 20. Back cover
[Electron Devices, IEEE Transactions on](#)
Volume 31, Issue 12, Dec 1984 Page(s):c4 - c4
Full Text: [PDF\(5176 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 21. Back cover
[Electron Devices, IEEE Transactions on](#)
Volume 32, Issue 12, Dec 1985 Page(s):c4 - c4
Full Text: [PDF\(6424 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 22. Integrated semiconductor magnetic field sensors
Baltes, H.P.; Popovic, R.S.;
[Proceedings of the IEEE](#)
Volume 74, Issue 8, Aug. 1986 Page(s):1107 - 1132
[AbstractPlus](#) | Full Text: [PDF\(3438 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 23. An investigation of the intrinsic delay (speed limit) in MTL//SUP 2/L
Berger, H.H.; Helwig, K.;
[Solid-State Circuits, IEEE Journal of](#)
Volume 14, Issue 2, Apr 1979 Page(s):327 - 337
[AbstractPlus](#) | Full Text: [PDF\(1968 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 24. Tunneling leakage in Ge preamorphized shallow junctions
Wen, D.-S.; Goodwin-Johansson, S.H.; Osburn, C.M.;
[Electron Devices, IEEE Transactions on](#)
Volume 35, Issue 7, Part 1, July 1988 Page(s):1107 - 1115
Digital Object Identifier 10.1109/16.3370
[AbstractPlus](#) | Full Text: [PDF\(756 KB\)](#) IEEE JNL
[Rights and Permissions](#)

**25. The efficient simulation of coupled point defect and impurity diffusion**

Kump, M.R.; Dutton, R.W.;

Computer-Aided Design of Integrated Circuits and Systems, IEEE Transactions on

Volume 7, Issue 2, Feb. 1988 Page(s):191 - 204

Digital Object Identifier 10.1109/43.3149

AbstractPlus | Full Text: PDF(1172 KB) IEEE JNLRights and Permissions1-25 | 26-47[Help](#) [Contact Us](#) [Privacy & Security](#) [IEEE.org](#)

© Copyright 2006 IEEE – All Rights Reserved

Indexed by
 Inspec



Welcome United States Patent and Trademark Office

☐ Search Results

BROWSE

SEARCH

IEEE XPLORE GUIDE

SUPPORT

Results for "((diffusion <near/3> length) <and> simulat??? <and> isolation <and> correct?..."

Your search matched 47 of 1436708 documents.

A maximum of 47 results are displayed, 25 to a page, sorted by Relevance in Descending order.

☒ e-mail printer friendly

» Search Options

[View Session History](#)[New Search](#)

Modify Search

☐ Check to search only within this results set
Display Format: ☒ Citation ☐ Citation & Abstract

» Key

IEEE JNL IEEE Journal or Magazine

IEE JNL IEE Journal or Magazine

IEEE CNF IEEE Conference Proceeding

IEE CNF IEE Conference Proceeding

IEEE STD IEEE Standard

[view selected items](#)[Select All](#) [Deselect All](#)

1-25 | 26-47

- ☐ 26. Elimination of charge-enhancement effects in GaAs FETs with a low-temperature grown GaAs buffer layer
McMorrow, D.; Weatherford, T.R.; Curtice, W.R.; Knudson, A.R.; Buchner, S.; Melinger, J.S.; Lan Hu Tran; Campbell, A.B.;
[Nuclear Science, IEEE Transactions on](#)
Volume 42, Issue 6, Part 1, Dec. 1995 Page(s):1837 - 1843
Digital Object Identifier 10.1109/23.488787
[AbstractPlus](#) | [Full Text: PDF\(656 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 27. Single-event phenomena in GaAs devices and circuits
McMorrow, D.; Weatherford, T.R.; Buchner, S.; Knudson, A.R.; Melinger, J.S.; Lan Hu Tran; Campbell, A.B., III;
[Nuclear Science, IEEE Transactions on](#)
Volume 43, Issue 2, Part 1, April 1996 Page(s):628 - 644
Digital Object Identifier 10.1109/23.490906
[AbstractPlus](#) | [References](#) | [Full Text: PDF\(1876 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 28. Cosmic and terrestrial single-event radiation effects in dynamic random access memories
Massengill, L.W.;
[Nuclear Science, IEEE Transactions on](#)
Volume 43, Issue 2, Part 1, April 1996 Page(s):576 - 593
Digital Object Identifier 10.1109/23.490902
[AbstractPlus](#) | [References](#) | [Full Text: PDF\(1820 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 29. Single-event effects rate prediction
Pickel, J.C.;
[Nuclear Science, IEEE Transactions on](#)
Volume 43, Issue 2, Part 1, April 1996 Page(s):483 - 495
Digital Object Identifier 10.1109/23.490895
[AbstractPlus](#) | [References](#) | [Full Text: PDF\(1400 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 30. Briefs
[Electron Devices, IEEE Transactions on](#)
Volume 43, Issue 1, Jan. 1996 Page(s):170
Digital Object Identifier 10.1109/TED.1996.477609
[AbstractPlus](#) | [Full Text: PDF\(1936 KB\)](#) IEEE JNL
[Rights and Permissions](#)

31. **Neutral base recombination and its influence on the temperature dependence of Early voltage and current gain-Early voltage product in UHV/CVD SiGe heterojunction bipolar transistors**
Joseph, A.J.; Cressler, J.D.; Richey, D.M.; Jaeger, R.C.; Hareme, D.L.;
[Electron Devices, IEEE Transactions on](#)
Volume 44, Issue 3, March 1997 Page(s):404 - 413
Digital Object Identifier 10.1109/16.556150
[AbstractPlus](#) | [References](#) | Full Text: [PDF\(348 KB\)](#) IEEE JNL
[Rights and Permissions](#)
32. **Effects of bandgap, lifetime, and other nonuniformities on diode laser thresholds and slope efficiencies**
Vurgaftman, I.; Meyer, J.R.;
[Selected Topics in Quantum Electronics, IEEE Journal of](#)
Volume 3, Issue 2, April 1997 Page(s):475 - 484
Digital Object Identifier 10.1109/2944.605697
[AbstractPlus](#) | [References](#) | Full Text: [PDF\(208 KB\)](#) IEEE JNL
[Rights and Permissions](#)
33. **IC failure analysis: magic, mystery, and science**
Soden, J.M.; Anderson, R.E.; Henderson, C.L.;
[Design & Test of Computers, IEEE](#)
Volume 14, Issue 3, July-Sept. 1997 Page(s):59 - 69
Digital Object Identifier 10.1109/54.605998
[AbstractPlus](#) | [References](#) | Full Text: [PDF\(876 KB\)](#) IEEE JNL
[Rights and Permissions](#)
34. **Charge collection and radiation hardness of a SOI microdosimeter for medical and space applications**
Bradley, P.D.; Rosenfeld, A.B.; Lee, K.K.; Jamieson, D.N.; Heiser, G.; Satoh, S.;
[Nuclear Science, IEEE Transactions on](#)
Volume 45, Issue 6, Part 1, Dec. 1998 Page(s):2700 - 2710
Digital Object Identifier 10.1109/23.736518
[AbstractPlus](#) | [References](#) | Full Text: [PDF\(1236 KB\)](#) IEEE JNL
[Rights and Permissions](#)
35. **1998 Index IEEE Transactions on Nuclear Science Vol. 45 (Author Index)**
[Nuclear Science, IEEE Transactions on](#)
Volume 45, Issue 6, Part 3, Dec. 1998 Page(s):1 - 26
Digital Object Identifier 10.1109/TNS.1998.736200
[AbstractPlus](#) | Full Text: [PDF\(604 KB\)](#) IEEE JNL
[Rights and Permissions](#)
36. **Thermal and tangential-momentum accommodation coefficients for N₂ colliding with surfaces of relevance to disk-drive air bearings derived from molecular beam scattering**
Rettner, C.T.;
[Magnetics, IEEE Transactions on](#)
Volume 34, Issue 4, Part 2, July 1998 Page(s):2387 - 2395
Digital Object Identifier 10.1109/20.703889
[AbstractPlus](#) | [References](#) | Full Text: [PDF\(268 KB\)](#) IEEE JNL
[Rights and Permissions](#)
37. **Development and characterization of high-efficiency Ga_{0.5}In_{0.5}P/GaAs/Ge dual- and triple-junction solar cells**
Karam, N.H.; King, R.R.; Cavicchi, B.T.; Krut, D.D.; Ermer, J.H.; Haddad, M.; Li Cai; Joslin, D.E.; Takahashi, M.; Eldredge, J.W.; Nishikawa, W.T.; Lillington, D.R.; Keyes, B.M.; Ahrenkiel, R.K.;
[Electron Devices, IEEE Transactions on](#)
Volume 46, Issue 10, Oct. 1999 Page(s):2116 - 2125
Digital Object Identifier 10.1109/16.792006
[AbstractPlus](#) | [References](#) | Full Text: [PDF\(352 KB\)](#) IEEE JNL
[Rights and Permissions](#)

- ☐ 38. **Level-specific lithography optimization for 1-Gb DRAM**
Wong, A.K.; Ferguson, R.; Mansfield, S.; Molless, A.; Samuels, D.; Schuster, R.; Thomas, A.;
[Semiconductor Manufacturing, IEEE Transactions on](#)
Volume 13, Issue 1, Feb. 2000 Page(s):76 - 87
Digital Object Identifier 10.1109/66.827347
[AbstractPlus](#) | [References](#) | Full Text: [PDF\(512 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 39. **Reliability monitoring and screening issues with ultrathin gate dielectric devices**
Abadeer, W.W.;
[Device and Materials Reliability, IEEE Transactions on](#)
Volume 1, Issue 1, March 2001 Page(s):60 - 68
Digital Object Identifier 10.1109/7298.946460
[AbstractPlus](#) | [References](#) | Full Text: [PDF\(216 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 40. **Author index**
[Electron Devices, IEEE Transactions on](#)
Volume 48, Issue 12, Dec. 2001 Page(s):2965 - 2984
Digital Object Identifier 10.1109/TED.2001.974738
[AbstractPlus](#) | Full Text: [PDF\(197 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 41. **Analytical charge collection and MTF model for photodiode-based CMOS imagers**
Lin, C.-S.S.; Mathur, B.P.; Chang, M.-C.F.;
[Electron Devices, IEEE Transactions on](#)
Volume 49, Issue 5, May 2002 Page(s):754 - 761
Digital Object Identifier 10.1109/16.998581
[AbstractPlus](#) | [References](#) | Full Text: [PDF\(546 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 42. **Heavy-ion broad-beam and microprobe studies of single-event upsets in 0.20- μm SiGe heterojunction bipolar transistors and circuits**
Reed, R.A.; Marshall, P.W.; Pickel, J.C.; Carts, M.A.; Fodness, B.; Niu, G.; Fritz, K.; Vizkelethy, G.; Dodd, P.E.; Irwin, T.; Cressler, J.D.; Krithivasan, R.; Riggs, P.; Prairie, J.; Randall, B.; Gilbert, B.; LaBel, K.A.;
[Nuclear Science, IEEE Transactions on](#)
Volume 50, Issue 6, Part 1, Dec. 2003 Page(s):2184 - 2190
Digital Object Identifier 10.1109/TNS.2003.821815
[AbstractPlus](#) | [References](#) | Full Text: [PDF\(439 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 43. **LET dependence of the charge collection efficiency of silicon microdosimeters**
Cornelius, I.M.; Rosenfeld, A.B.; Siegele, R.; Cohen, D.D.;
[Nuclear Science, IEEE Transactions on](#)
Volume 50, Issue 6, Part 1, Dec. 2003 Page(s):2373 - 2379
Digital Object Identifier 10.1109/TNS.2003.820740
[AbstractPlus](#) | [References](#) | Full Text: [PDF\(853 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 44. **Subject Index**
[Applied Superconductivity, IEEE Transactions on](#)
Volume 13, Issue 4, Dec. 2003 Page(s):3931 - 4012
Digital Object Identifier 10.1109/TASC.2003.1255505
[AbstractPlus](#) | Full Text: [PDF\(935 KB\)](#) IEEE JNL
[Rights and Permissions](#)
- ☐ 45. **Author Index**
[Applied Superconductivity, IEEE Transactions on](#)
Volume 13, Issue 4, Dec. 2003 Page(s):3878 - 3931
Digital Object Identifier 10.1109/TASC.2003.1255504

[AbstractPlus](#) | Full Text: [PDF\(678 KB\)](#) IEEE JNL
[Rights and Permissions](#)

- ☐ 46. Atmospheric neutron effects in advanced microelectronics, standards and applications
Leray, J.-L.; Baggio, J.; Ferlet-Cavrois, V.; Flament, O.;
[Integrated Circuit Design and Technology, 2004. ICICDT '04. International Conference on](#)
2004 Page(s):311 - 321
Digital Object Identifier 10.1109/ICICDT.2004.1309974

[AbstractPlus](#) | Full Text: [PDF\(826 KB\)](#) IEEE CNF
[Rights and Permissions](#)

- ☐ 47. High-current characterization of dual-damascene copper interconnects in SiO₂- and low-
k interlevel dielectrics for advanced CMOS semiconductor technologies
Voldman, S.; Gauthier, R.; Morrisseau, K.; Hargrove, M.; McGahay, V.; Gross, V.;
[Reliability Physics Symposium Proceedings, 1999. 37th Annual. 1999 IEEE International](#)
23-25 March 1999 Page(s):144 - 153
Digital Object Identifier 10.1109/RELPHY.1999.761606

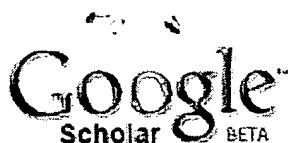
[AbstractPlus](#) | Full Text: [PDF\(948 KB\)](#) IEEE CNF
[Rights and Permissions](#)

[1-25](#) | [26-47](#)

[Help](#) [Contact Us](#) [Privacy & Security](#) [IEEE.org](#)

© Copyright 2006 IEEE – All Rights Reserved

indexed by
 Inspec®



"diffusion size" isolation

Search

[Advanced Scholar Search](#)
[Scholar Preferences](#)
[Scholar Help](#)

Scholar [All articles](#) [Recent articles](#)

Results 1 - 10 of about 18 for "**diffusion size**" **isolation**. (0.14 seconds)

All Results

[G Scott](#)

[F Faccio](#)

[M Anderson](#)

[J Lutze](#)

[M Rubin](#)

NMOS drive current reduction caused by transistor layout and trenchisolation induced stress

G Scott, J Lutze, M Rubin, F Nouri, M Manley, P ... - Electron Devices Meeting, 1999. IEDM Technical Digest. ..., 1999 - [ieeexplore.ieee.org](#)
 ... Mobility reduction, induced by stress from the trench **isolation** edge, is the root ... strongly with distance from the trench edge, and with overall **diffusion size**. ...
[Cited by 24](#) - [Related Articles](#) - [Web Search](#) - [BL Direct](#)

Single Event Effects in Static and Dynamic Registers in a 0.25 μ m CMOS Technology - group of 5 »

F Faccio, K Kloukinas, A Marchioro, T Calin, J ... - IEEE Trans. Nucl. Sci, 1999 - [cern.ch](#)
 ... the presence of retrograde wells and the use of Shallow Trench **Isolation** (STI ... have chosen the minimum gate length and the minimum drain **diffusion size** for all ...
[Cited by 25](#) - [Related Articles](#) - [View as HTML](#) - [Web Search](#) - [BL Direct](#)

A fully scaled submicron direct write E-beam CMOS technology for ULSI digital applications

RSL Lutze, HP Vyas, JST Huang - 1984 International Electron Devices Meeting, 1984 - [ieeexplore.ieee.org](#)
 ... having minimum size contacts which further scale the **diffusion size** and resultant ...
 Device **isolation** measurements showed that all impurity profiles and spacings ...
[Web Search](#)

Improvement of the Position Resolution of the CCD for X-Ray Use

K Yoshita, H Tsunemi, E Miyata, KC Gendreau, MW ... - IEEE TRANSACTIONS ON NUCLEAR SCIENCE, 1999 - [ieeexplore.ieee.org](#)
 ... This indicates that the charge **isolation** is worse for interphase **isolation** than doping-induced **isolation**. ... The characteristic **diffusion size** of the charge cloud ...
[Cited by 2](#) - [Related Articles](#) - [Web Search](#) - [BL Direct](#)

Single Event Effects in Static and Dynamic Registers in a 0.25 μ m CMOS Technology F. Faccio1, K. ...

T Calin, J Cosculluela, M Nicolaidis - IEEE TRANSACTIONS ON NUCLEAR SCIENCE, 1999 - [ieeexplore.ieee.org](#)
 ... the presence of retrograde wells and the use of Shallow Trench **Isolation** (STI ... have chosen, the minimum gate length and the minimum drain **diffusion size** for all ...
[Related Articles](#) - [Web Search](#)

The STAR time projection chamber: a unique tool for studying high multiplicity events at RHIC - group of 19 »

M Anderson, J Berkovitz, W Betts, R Bossingham, F ... - Nuclear Inst. and Methods in Physics Research, A, 2003 - Elsevier
 ... Pad size 2:85 mm \times 11:5 mm 6:20 mm \times 19:5 mm **Isolation** gap between pads 0:5 mm 0:5 mm ... There is a 0:5 mm **isolation** gap between pads. ...
[Cited by 102](#) - [Related Articles](#) - [Web Search](#)

A methodology for pre-determination of bipolar SPICE modelparameters in BiCMOS technology

S Aggarwal, A Juge - Microelectronic Test Structures, 1993. ICMTS 1993. ..., 1993 - [ieeexplore.ieee.org](#)
 ... r/n Vertical access resistance narrow resistor dwd Lateral **diffusion** (size variation) narrow ... for collector (contact, in & ext.) and one layer for **isolation**. ...
[Related Articles](#) - [Web Search](#)

Nuclear Export of Vpr Is Required for Efficient Replication of Human Immunodeficiency

Virus Type 1 ... - group of 5 »

MP Sherman, CMC de Noronha, LA Eckstein, J Hataye, ... - Journal of Virology, 2003 - jvi.asm.org

... Since the backbone is larger (90 kDa) than the passive **diffusion size** of the NPC (60 kDa), its import and export occur by active ... PBMC **isolation** and infection ...

Cited by 13 - Related Articles - Web Search - BL Direct

Airborne Nanostructured Particles and Occupational Health - group of 2 »

AD Maynard, ED Kuempel - Journal of Nanoparticle Research, 2005 - Springer

Page 1. Perspectives Airborne nanostructured particles and occupational health Andrew D. Maynard*, and Eileen D. Kuempel Project ...

Cited by 4 - Related Articles - Web Search - BL Direct

[book] Mobile Particulate Systems

E Guazzelli, L Oger - 1995 - books.google.com

... If the particle is symmetric so that these two centres coincide, the particles do not rotate in **isolation** in Stokes flow (see chpt 2 by Davis)

Cited by 3 - Related Articles - Web Search - Library Search

Google ►

Result Page: 1 2 **Next**

"diffusion size" isolation

Search

[Google Home](#) - [About Google](#) - [About Google Scholar](#)

©2006 Google



"diffusion size" parameter simulation

Search

[Advanced Scholar Search](#)
[Scholar Preferences](#)
[Scholar Help](#)

Scholar [All articles](#) [Recent articles](#) Results 1 - 10 of about 37 for "**diffusion size**" **parameter simulation**. (0.20 seconds)

All Results

[F Faccio](#)
[J Cosculluela](#)
[M Nicolaidis](#)
[K Kloukinas](#)
[A Marchioro](#)

Single Event Effects in Static and Dynamic Registers in a 0.25 μ m CMOS Technology - group of 5 »

F Faccio, K Kloukinas, A Marchioro, T Calin, J ... - IEEE Trans. Nucl. Sci, 1999 - cern.ch
 ... chosen the minimum gate length and the minimum drain **diffusion size** for all ... The **simulation** has been performed using the typical set of **parameters** given by ...
[Cited by 25](#) - [Related Articles](#) - [View as HTML](#) - [Web Search](#) - [BL Direct](#)

Mass and size effect in condensed fluids Rare gases and ionic liquids - group of 2 »

F Lantelme - Molecular Physics, 1982 - Taylor & Francis
 ... determinations with the results of **simulation** experiments in ... Model fluid **Diffusion Size Packing** ... under investigation is a very sensitive **parameter** ; when this ...
[Cited by 5](#) - [Related Articles](#) - [Web Search](#)

Role of source/drain junction on plasma induced gate charging damage in N MOSFET

W Lin, G Sery - Plasma-and Process-Induced Damage, 2001 6th International ..., 2001 - ieeexplore.ieee.org
 ... Increasing source and drain **diffusion size** can enhance charging ... **Simulation** based on this model suggests that ... quality and device structure **parameters** such as ...
[Cited by 5](#) - [Related Articles](#) - [Web Search](#)

Experimental evidence of a **diffusion size effect in thin Au films on Ag (111) - group of 6 »**

MG Goldiner, VB Sapozhnikov, M Klaua, K Meinel - Journal of Physics: Condensed Matter, 1991 - iop.org
 ... 3.4. Volume diffusion **parameters** ... Page 5. Experimental **diffusion size** effect in Au/Ag(III) 5483 ... 4. **Simulation** of diffusion kinetics ...
[Cited by 3](#) - [Related Articles](#) - [Web Search](#)

EwSim-Electronic Warfare Real Time **Simulation in the Visual and Infrared Wavelength Range**

C Hedberg, L Tydén, C Wigren - FOI-rapport, FOI-R--0709--SE, Dec, 2000 - foi.se
 ... 3.4.3 **Diffusion size** ... specialists can therefore have a different set of **parameters** than an ... environment for virtual reality and real-time **simulation** applications ...
[Cited by 2](#) - [Related Articles](#) - [Web Search](#)

A VLSI design system for teaching introduction to microelectronics - group of 2 »

E Sicard, A Rubio, K Kinashita, T INSA-DGE - Education, IEEE Transactions on, 1992 - ieeexplore.ieee.org
 ... Control the **diffusion size** and stop at 1.2 pm. ... The transistor **parameters**, parasitic capacitors, and nodes are ... Schematic capture and logic **simulation** are widely ...
[Cited by 2](#) - [Related Articles](#) - [Web Search](#) - [BL Direct](#)

User's Manual for LAMOCA 3.0 - group of 2 »

AKLMCK Simulator - dunham.ee.washington.edu
 ... The "**parameter.inp**" file tends to contain **parameter** values that define environments of the **simulation**, such as the domain size, boundary conditions on ...
[Related Articles](#) - [View as HTML](#) - [Web Search](#)

... POPULATION DYNAMICS MODEL COMBINED WITH A STATISTICAL **PARAMETER ESTIMATION PROCEDURE: APPLICATION ...**

B Faugeras, O Maury - blaise.faugeras.free.fr
 ... We develop an advection-**diffusion size**-structured fish population ... for the integration of the **simulation** model. ... step we address the **parameter** estimation problem ...
[Related Articles](#) - [View as HTML](#) - [Web Search](#)

Mathematical conservation ecology: A one-predator-two-prey system as case study - group of 4 »

J Grasman, F van den Bosch, OA van Herwaarden - Bulletin of Mathematical Biology, 2001 - Springer
... model. In the present study we consider a one-predator-two-prey model with **parameter** values that have biological significance. ...
[Related Articles](#) - [Web Search](#) - [BL Direct](#)

Effects of specimen size on the

AV Vaisleibt, MG Goldiner - J. Phys. D Appl. Phys, 1982 - iop.org
... In papers [W] in the analysis of Au diffusion into Si crystal of unlimited size only one length **parameter** l a p-' has been taken into consideration. ...
[Web Search](#)

Goooooogle ►

Result Page: 1 2 3 4 **Next**

[Google Home](#) - [About Google](#) - [About Google Scholar](#)

©2006 Google



"diffusion size" parameter simulation

Search

[Advanced Scholar Search](#)
[Scholar Preferences](#)
[Scholar Help](#)

Scholar [All articles](#) [Recent articles](#) Results 11 - 20 of about 37 for "diffusion size" parameter simulation. (0.28 seconds)

All Results

[F Faccio](#)

[J Cosculluela](#)

[M Nicolaidis](#)

[K Kloukinas](#)

[A Marchioro](#)

[Characterization of membrane domains by frap experiments at variable observation areas - group of 3 »](#)

L Salomé, JL Cazeils, A Lopez, JF Tocanne - European Biophysics Journal, 1998 - Springer

... Snapshots are shown illustrating three steps of the **simulation**: A before bleaching,

B ... a general rule for the behavior of the dif- fusion **parameters** D and M ...

Cited by 16 - [Related Articles](#) - [Web Search](#) - [BL Direct](#)

[Single Event Effects in Static and Dynamic Registers in a O. 25. tm CMOS Technology F. Faccio1, K. ...](#)

T Calm, J Cosculluela, M Nicolaidis - IEEE TRANSACTIONS ON NUCLEAR SCIENCE, 1999 -

ieeexplore.ieee.org

... the minimum gate length and the minimum drain **diffusion size** for all NMOS ... The **simulation**

has' been performed using the typical set of **parameters** given by ...

[Related Articles](#) - [Web Search](#)

[Automatic device layout generation for analog layout retargeting - group of 2 »](#)

R Hartono, N Jangkrarn, S Bhattacharya, CJ ... - VLSI Design, 2005. 18th International Conference on,

2005 - ieeexplore.ieee.org

... and d is the **diffusion size** calculated from ... netlist and the technology process

parameters, the synthesis engine invokes multiple circuit **simulation** runs during ...

Cited by 1 - [Related Articles](#) - [Web Search](#)

[Continuous thermal histories from closure profiles](#)

TM Harrison, M Grove, OM Lovera, PK Zeitler - Thermochemistry, Reviews in Mineralogy & Geochemistry,

this, 2005 - sims.ess.ucla.edu

... C. The magnitude of this range would be of less concern if it could be reported

that the compositional and **diffusion size parameters** were routinely measured. ...

Cited by 1 - [Related Articles](#) - [View as HTML](#) - [Web Search](#)

[Deuterium NMR of polymer dispersed liquid crystals - group of 3 »](#)

A Golemme, S Zumer, JW Doane, ME Neubert - Physical Review A, 1988 - APS

... on several factors which include self-**diffusion**, **size**, shape of ... The asymmetry **parameter**

iq(r) can be different from ... Gq is calculated by a **simulation** of this ...

Cited by 34 - [Related Articles](#) - [Web Search](#)

[A Framework For Architecture Level Power Estimation](#)

田中英彦 - ww.mtl.tu-tokyo.ac.jp

... **parameters** are extracted from the layout and simulated again by SPICE. Power analysis

is only one of many analysis SPICE can perform. Because SPICE **simulation** ...

[Related Articles](#) - [View as HTML](#) - [Web Search](#)

[The STAR time projection chamber: a unique tool for studying high multiplicity events at RHIC - group of 19 »](#)

M Anderson, J Berkovitz, W Betts, R Bossingham, F ... - Nuclear Inst. and Methods in Physics Research, A,

2003 - Elsevier

... the two pad plane sector geometries were verified through **simulation** and testing ...

and two-track resolution show a dramatic dependence on the design **parameters**. ...

Cited by 102 - [Related Articles](#) - [Web Search](#)

[Kinetic approach to multiple pathway diffusion with traps - group of 4 »](#)

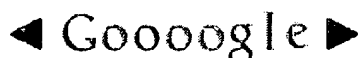
MG Goldiner, AV Vaysleyb - Physical Review B, 1995 - APS

... Antoniadis, in Process and Device **Simulation** for MOS ... the determination of the critical

parameters of the ... The **diffusion size** effect predicted for Au diffusion in ...
[Related Articles](#) - [Web Search](#) - [BL Direct](#)

True multi-component mixed-bed ion-exchange modeling - group of 2 »
Y Jia, GL Foutch - Reactive and Functional Polymers, 2004 - Elsevier
... The **simulation** of multi-component MBIE has ... diffusivity is an important **parameter**
in modeling ... dispersion, film and intraparticle **diffusion**, size exclusion and ...
[Related Articles](#) - [Web Search](#)

Investigation of Volatility Method for Measuring Aqueous Sulfuric Acid on Mixed Aerosols -
group of 3 »
Findings were supported by Dinger - Aerosol Science & Technology, 2002 - Taylor & Francis
... of the droplets is included in the calculations by evaluating the **parameters** M p ...
Using a Metropolis Monte Carlo **simulation** (Hale and Kathmann 1996) the interac ...
[Cited by 2](#) - [Related Articles](#) - [Web Search](#) - [BL Direct](#)



Result Page: **Previous** [1](#) [2](#) [3](#) [4](#) **Next**

[Google Home](#) - [About Google](#) - [About Google Scholar](#)

©2006 Google



"diffusion size" parameter simulation

Search

[Advanced Scholar Search](#)
[Scholar Preferences](#)
[Scholar Help](#)

Scholar All articles [Recent articles](#) Results 21 - 30 of about 37 for "diffusion size" parameter simulation. (0.18 seconds)

All Results

[F Faccio](#)

[J Cosculluela](#)

[M Nicolaidis](#)

[K Kloukinas](#)

[A Marchioro](#)

[Online Monitoring of Nanoparticle Contamination in Reactive Gases](#)

O Schmid, MB Trueblood, DE Hagen, PD Whitefield - Journal of the IEST, 2004 - IEST
 ... 50 and d 0, depend on gas type and other **parameters**. There are es- sentially
 two methods to adjust d 50 to process-specific require- ments. ...
[Related Articles](#) - [Web Search](#) - [BL Direct](#)

[An electron paramagnetic resonance study of rotational and translational motion in solution](#)

LL Jones, RN Schwartz - Molecular Physics, 1981 - Taylor & Francis
 ... 1"478 _+ 0"002 mT, giso = 2.00601), it was decided to use the magnetic **parameters**
 determined in that system rather than attempt another rigid limit **simulation**. ...
[Cited by 5](#) - [Related Articles](#) - [Web Search](#)

[A Database-Driven VLSI Design System - group of 3 »](#)

KC Chu, JP Fishburn, P Honeyman, YE Lien - Computer-Aided Design of Integrated Circuits and Systems, ...,
 1986 - [ieeexplore.ieee.org](#)
 ... giving the name of the technology as a **parameter**. ... to a switch-level logic **simulator**,
 a plotter ... transistor, type, polysili- con size, **diffusion size**, the four ...
[Cited by 1](#) - [Related Articles](#) - [Web Search](#)

[Navigation and planning in an unknown environment using vision and a cognitive map - group of 2 »](#)

N Cuperlier, M Quoy, P Gaussier, C Giovanangelli - science.uva.nl
 ... recognition threshold (section 3) and the **diffusion size** of the ... The second **parameter**
 has to be tuned for ... In From Animals to Animats : **Simulation** of Adaptive ...
[Related Articles](#) - [View as HTML](#) - [Web Search](#)

[A Framework For Architecture Level Power Estimation](#)

C lwama - [ww.mtl.tu-tokyo.ac.jp](#)
 ... the circuit is created, actual dimen- sions and parasitic **parameters** are extracted ...
 Be- cause SPICE **simulation** is expensive, PowerMill [10] has been developed ...
[Related Articles](#) - [View as HTML](#) - [Web Search](#)

[Acoustic cues for 3-D shape information - group of 2 »](#)

D Rocchesso - Proc. of the 2001 Int. Conf. on Auditory Display, 2001 - [acoustics.hut.fi](#)
 ... that allows independent control of wall absorption, **diffusion**, **size**, and shape.
 Namely, the shape control is exerted by changing the **parameters** of allpass ...
[Cited by 19](#) - [Related Articles](#) - [View as HTML](#) - [Web Search](#)

[Optimisation Strategies IN Diffusion Tensor MR Imaging](#)

K Institutet, S Stockholm - [mr.imaging-ks.nu](#)
 ... the diffusion tensor the mean **diffusion** (**size** of the ... The **simulation** results were
 also complemented with data ... pulse) that imaging starts TE MR scan **parameter**. ...
[Related Articles](#) - [View as HTML](#) - [Web Search](#)

[Can one hear the volume of a shape? - group of 5 »](#)

D Rocchesso, L Ottaviani, DS e Tecnologico - Applications of Signal Processing to Audio and Acoustics, ...,
 2001 - [ieeexplore.ieee.org](#)
 ... that allows independent con- trol of wall absorption, **diffusion**, **size**, and shape.
 Namely, the shape control is exerted by changing the **parameters** of ailpass fil ...
[Cited by 12](#) - [Related Articles](#) - [Web Search](#)

[Symple: a symbolic layout tool for bipolar and MOS VLSI - group of 2 »](#)

KSB Szabo, JM Leask, MI Elmasry - Communications, Speech and Vision, IEE Proceedings I, 1988 -
ieeexplore.ieee.org

... t to modify geometry according to various **parameters** and output B in A I n R B Fig.

3 design rules, as well as n-well, p-well or twin-tub CMOS technologies. ...

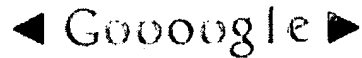
[Related Articles](#) - [Web Search](#)

[book] [Particle-Lung Interactions](#)

P Gehr, J Heyder - 2000 - [books.google.com](#)

Page 1. PARTICLE-LUNG INTERACTIONS Th iBO fl o l'll' Page 2. LUNG BIOLOGY IN
HEALTH AND DISEASE Executive Editor Claude Lenfant Director ...

[Cited by 8](#) - [Related Articles](#) - [Web Search](#) - [BL Direct](#)



Result Page: [Previous](#) [1](#) [2](#) [3](#) [4](#) [Next](#)

[Google Home](#) - [About Google](#) - [About Google Scholar](#)

©2006 Google



"diffusion size" parameter simulation

Search

[Advanced Scholar Search](#)
[Scholar Preferences](#)
[Scholar Help](#)

Scholar [All articles](#) [Recent articles](#)

Results 31 - 37 of 37 for "diffusion size" parameter simulation. (0.19 seconds)

All Results

[F Faccio](#)

[J Cosculluela](#)

[M Nicolaidis](#)

[K Kloukinas](#)

[A Marchioro](#)

[Review August 1999 Vol. 40, No. 3 - group of 2 »](#)

J Eaton, S Kortum - [ingentaconnect.com](#)

... results, they have quite different implications for **simulation**. ... The **parameter** α it reflects the ... In the absence of **diffusion**, **size** bias can be eliminated by ...

[Related Articles](#) - [Web Search](#)

[\[book\] Chemical Physics of Thin Film Deposition Processes for Micro- And Nano-Technologies - group of 2 »](#)

Y Pauleau - 2002 - [books.google.com](#)

... chemical processing for nanodevice elaboration, molecular dynamics **simulation** of thin ... 7) epitaxial growth of metastable compounds, (8) major **parameters** to be ...

Cited by 1 - [Related Articles](#) - [Web Search](#) - [Library Search](#)

[Particle formation, deposition, and particle induced corrosion in large-scale medium-speed diesel ... - group of 3 »](#)

J Lyyr nen - [vtt.fi](#)

... size distribution from a diesel engine, excluding the **simulation** of atmospheric ... changes in measurement conditions, they were selected as **parameters** to compare ...

[Related Articles](#) - [View as HTML](#) - [Web Search](#)

[\[book\] Mobile Particulate Systems](#)

E Guazzelli, L Oger - 1995 - [books.google.com](#)

Page 1. ii kluwer the language of science Page 2. Mobile Particulate Systems

Page 3. NATO ASI Series Advanced Science Institutes Series ...

Cited by 3 - [Related Articles](#) - [Web Search](#) - [Library Search](#)

[Anisotropy in CdSe quantum rods - group of 4 »](#)

L Li - Other Information: TH: Thesis (Ph. D, 2003 - [osti.gov](#)

... TEB), has been used to study the rotational **diffusion**, **size**, shape, and ... For example, according to a numerical **simulation** performed on the lyotropic liquid ...

[Web Search](#) - [Library Search](#)

[Characterisation of Exhaust Particulate Emissions from Road Vehicles - group of 2 »](#)

FF Programme - [lat.eng.auth.gr](#)

... 3. Health effects associated with selected **parameters** of vehicle exhaust particulate ...

Simulation of real world conditions is a challenge which is key to real ...

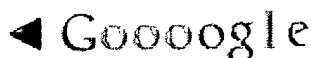
[Related Articles](#) - [View as HTML](#) - [Web Search](#)

[\[PS\] Botanical Computing: A Developmental Approach to Generating Interconnect Topologies on an Amorphous ... - group of 4 »](#)

DN Coore - 1922 - [swiss.ai.mit.edu](#)

... 16 Page 17. 3. it represents an unprecedented level of control over macroscopic properties derived from the manipulation of microscopic **parameters**. ...

Cited by 36 - [Related Articles](#) - [View as HTML](#) - [Web Search](#) - [Library Search](#)



Result Page: [Previous](#) [1](#) [2](#) [3](#) [4](#)

"diffusion size" parameter simulation

[Google Home](#) - [About Google](#) - [About Google Scholar](#)

©2006 Google